

# PMCM6501UNE 20 V, N-channel Trench MOSFET 30 May 2017

Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a 6 bumps Wafer Level Chip-Size Package (WLCSP) using Trench MOSFET technology.

#### 2. Features and benefits

- Low threshold voltage
- Ultra small package: 0.98 × 1.48 × 0.35 mm
- Trench MOSFET technology •
- ElectroStatic Discharge (ESD) protection > 2 kV HBM •

#### 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

#### 4. Quick reference data

#### Table 1. Quick reference data

| Symbol                 | Parameter                        | Conditions   |     | Min | Тур | Max | Unit |
|------------------------|----------------------------------|--|-----|-----|-----|-----|------|
| V <sub>DS</sub>        | drain-source voltage             | T <sub>j</sub> = 25 °C   |     | -   | -   | 20  | V    |
| V <sub>GS</sub>        | gate-source voltage              |  |     | -8  | -   | 8   | V    |
| I <sub>D</sub>         | drain current                    | $V_{GS}$ = 4.5 V; $T_{amb}$ = 25 °C; t ≤ 5 s                   | [1] | -   | -   | 8.7 | А    |
| Static characteristics |                                  |  |     |     |     |     |      |
| R <sub>DSon</sub>      | drain-source on-state resistance | $V_{GS}$ = 4.5 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 25 °C |     | -   | 17  | 21  | mΩ   |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>

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20 V, N-channel Trench MOSFET

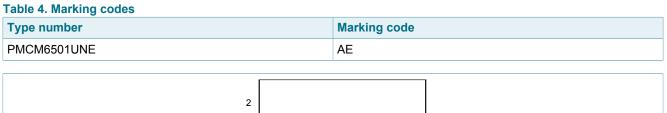
## 5. Pinning information

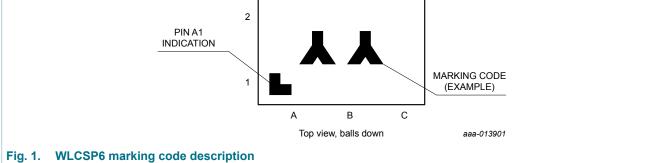
| Table 2. F | Pinning inf | formation   |   |                |
|------------|-------------|-------------|---|----------------|
| Pin        | Symbol      | Description | Simplified outline                          | Graphic symbol |
| A1         | G           | gate        | 1 2   | D              |
| A2         | S           | source      |   |                |
| B1         | S           | source      | в   | G ← → ☆ ↓      |
| B2         | S           | source      |   |                |
| C1         | D           | drain       | c   |                |
| C2         | D           | drain       | Transparent top view<br>WLCSP6 (WLCSP6_3-2) | S<br>017aaa255 |

# 6. Ordering information

| Table 3. Ordering information |         |  |            |  |  |  |
|-------------------------------|---------|--|------------|--|--|--|
| Type number                   | Package |  |            |  |  |  |
|                               | Name    | Description                                    | Version    |  |  |  |
| PMCM6501UNE                   | WLCSP6  | wafer level chip-size package; 6 bumps (3 x 2) | WLCSP6_3-2 |  |  |  |

# 7. Marking





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#### 8. Limiting values

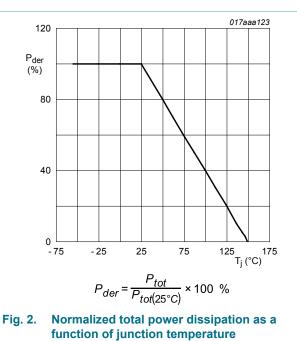
#### Table 5. Limiting values

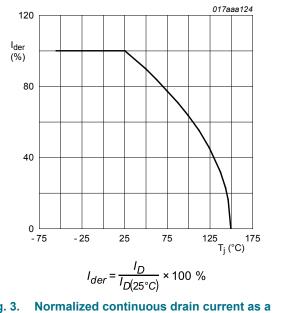
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions   |     | Min | Мах  | Unit |
|------------------|-------------------------|--|-----|-----|------|------|
| V <sub>DS</sub>  | drain-source voltage    | T <sub>j</sub> = 25 °C                                     |     | -   | 20   | V    |
| V <sub>GS</sub>  | gate-source voltage     |  |     | -8  | 8    | V    |
| I <sub>D</sub>   | drain current           | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s | [1] | -   | 8.7  | А    |
|                  |                         | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C          | [1] | -   | 6.6  | А    |
|                  |                         | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C         | [1] | -   | 4.2  | А    |
| I <sub>DM</sub>  | peak drain current      | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$      |     | -   | 27   | А    |
| P <sub>tot</sub> | total power dissipation | T <sub>amb</sub> = 25 °C                                   | [2] | -   | 556  | mW   |
|                  |                         |  | [1] | -   | 1.3  | W    |
|                  |                         | T <sub>sp</sub> = 25 °C                                    |     | -   | 12.5 | W    |
| Tj               | junction temperature    |  |     | -55 | 150  | °C   |
| T <sub>amb</sub> | ambient temperature     |  |     | -55 | 150  | °C   |
| T <sub>stg</sub> | storage temperature     |  |     | -65 | 150  | °C   |
| Source Drai      | n Diode                 |  | ·   |     |      |      |
| I <sub>S</sub>   | source current          | T <sub>amb</sub> = 25 °C                                   | [1] | -   | 1.2  | А    |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.

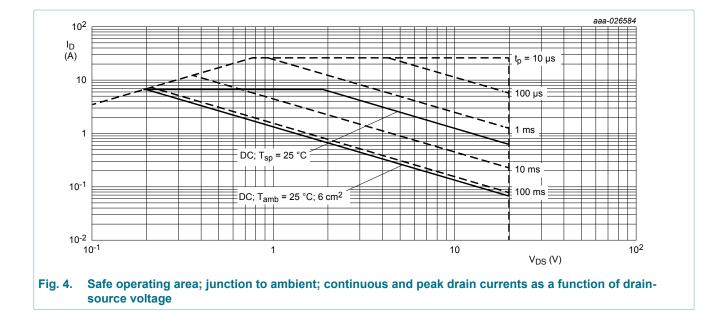






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# 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

|                       | indi characteristics                                   |             |     |     |     |     |      |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| Symbol                | Parameter  | Conditions  |     | Min | Тур | Max | Unit |
| R <sub>th(j-a)</sub>  | thermal resistance                                     | in free air | [1] | -   | 180 | 225 | K/W  |
|                       | from junction to<br>ambient                            |             | [2] | -   | 65  | 85  | K/W  |
|                       |  |             | [3] | -   | 75  | 95  | K/W  |
|                       |  | t ≤ 5 s     | [3] | -   | 45  | 55  | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance<br>from junction to solder<br>point |             |     | -   | 5   | 10  | K/W  |

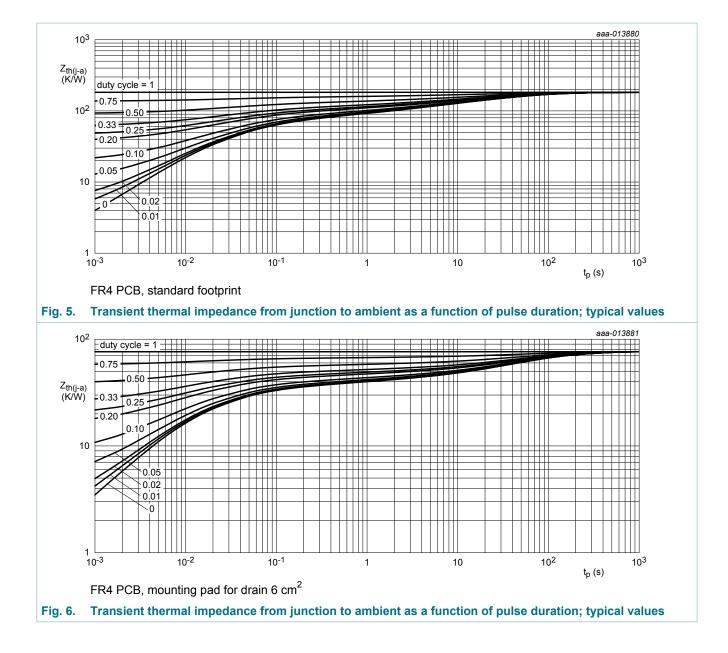
Device mounted on an FR4 Printed-Circuit Board (PCB), single sided-copper; tin-plated and standard footprint. Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain, 4 layer, 1 cm<sup>2</sup> [1]

[2]

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

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#### 20 V, N-channel Trench MOSFET



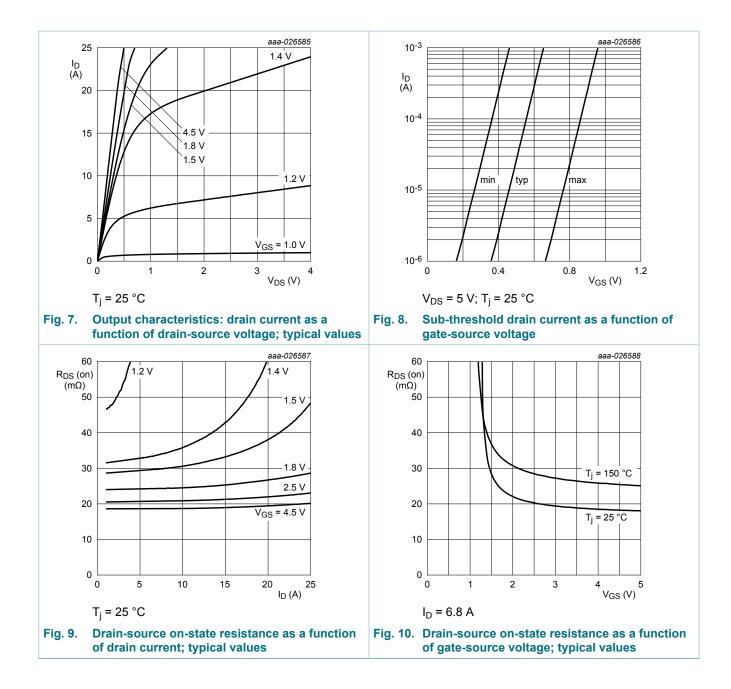
20 V, N-channel Trench MOSFET

# **10. Characteristics**

| Symbol               | Parameter                           | Conditions  | Min | Тур | Max  | Unit |
|----------------------|-------------------------------------|---|-----|-----|------|------|
| Static chara         | acteristics                         |   | 1   |     | - 1  | _,   |
| V <sub>(BR)DSS</sub> | drain-source<br>breakdown voltage   | $I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C                                     | 20  | -   | -    | V    |
| V <sub>GSth</sub>    | gate-source threshold voltage       | $I_D$ = 250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C                               | 0.4 | 0.6 | 0.9  | V    |
| I <sub>DSS</sub>     | drain leakage current               | V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C             | -   | -   | 1    | μA   |
| I <sub>GSS</sub>     | gate leakage current                | V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C              | -   | -   | 10   | μA   |
|                      |                                     | $V_{GS}$ = -8 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                                    | -   | -   | -10  | μA   |
|                      |                                     | $V_{GS}$ = 4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                                   | -   | -   | 1    | μA   |
|                      |                                     | $V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                                  | -   | -   | -1   | μA   |
|                      |                                     | $V_{GS}$ = 2.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                                   | -   | -   | 200  | nA   |
|                      |                                     | $V_{GS}$ = -2.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                                  | -   | -   | -200 | nA   |
| R <sub>DSon</sub>    | drain-source on-state<br>resistance | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 25 °C             | -   | 17  | 21   | mΩ   |
|                      |                                     | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 150 °C            | -   | 25  | 29   | mΩ   |
|                      |                                     | V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 25 °C             | -   | 20  | 25   | mΩ   |
|                      |                                     | V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 2 A; T <sub>j</sub> = 25 °C             | -   | 22  | 32   | mΩ   |
|                      |                                     | V <sub>GS</sub> = 1.5 V; I <sub>D</sub> = 1 A; T <sub>j</sub> = 25 °C             | -   | 30  | 45   | mΩ   |
| 9fs                  | forward<br>transconductance         | V <sub>DS</sub> = 5 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 25 °C               | -   | 40  | -    | S    |
| R <sub>G</sub>       | gate resistance                     | f = 1 MHz; T <sub>j</sub> = 25 °C   | -   | 1.2 | -    | Ω    |
| Dynamic ch           | aracteristics                       |   |     |     |      |      |
| Q <sub>G(tot)</sub>  | total gate charge                   | $V_{DS}$ = 10 V; I <sub>D</sub> = 3 A; V <sub>GS</sub> = 4.5 V;                   | -   | 19  | 28   | nC   |
| Q <sub>GS</sub>      | gate-source charge                  | T <sub>j</sub> = 25 °C  | -   | 1.2 | -    | nC   |
| Q <sub>GD</sub>      | gate-drain charge                   |   | -   | 5.8 | -    | nC   |
| C <sub>iss</sub>     | input capacitance                   | $V_{DS} = 10 \text{ V}; \text{ f} = 1 \text{ MHz}; \text{ V}_{GS} = 0 \text{ V};$ | -   | 105 | -    | pF   |
| C <sub>oss</sub>     | output capacitance                  | T <sub>j</sub> = 25 °C  | -   | 19  | -    | pF   |
| C <sub>rss</sub>     | reverse transfer capacitance        |   | -   | 18  | -    | pF   |
| t <sub>d(on)</sub>   | turn-on delay time                  | $V_{DS}$ = 10 V; I <sub>D</sub> = 6.6 A; V <sub>GS</sub> = 4.5 V;                 | -   | 7.3 | -    | ns   |
| t <sub>r</sub>       | rise time                           | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$  | -   | 28  | -    | ns   |
| t <sub>d(off)</sub>  | turn-off delay time                 | 1   | -   | 100 | -    | ns   |
| t <sub>f</sub>       | fall time                           |   | -   | 46  | -    | ns   |
| Source-drai          | n diode                             |   |     |     |      |      |
| V <sub>SD</sub>      | source-drain voltage                | I <sub>S</sub> = 1.2 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C             | -   | 0.6 | 1.2  | V    |

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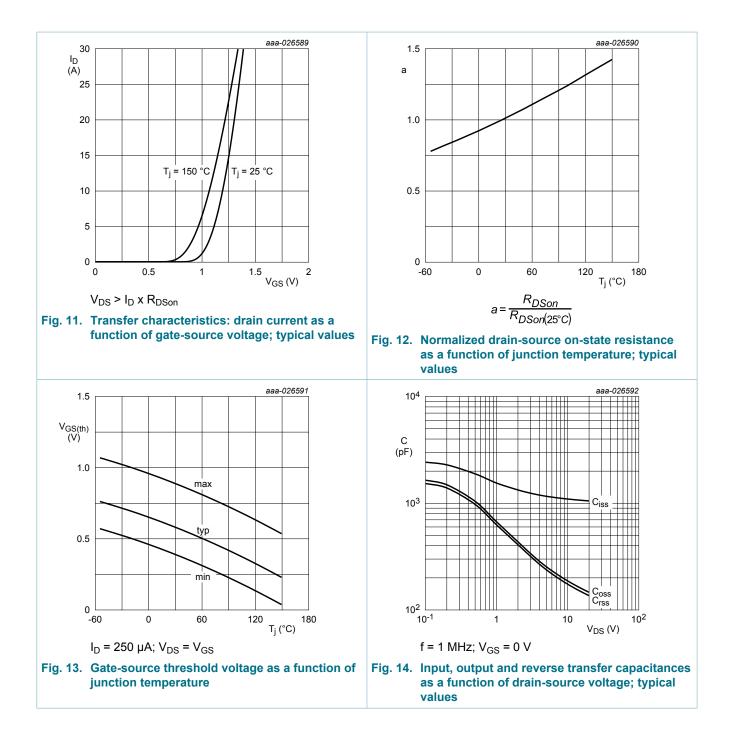
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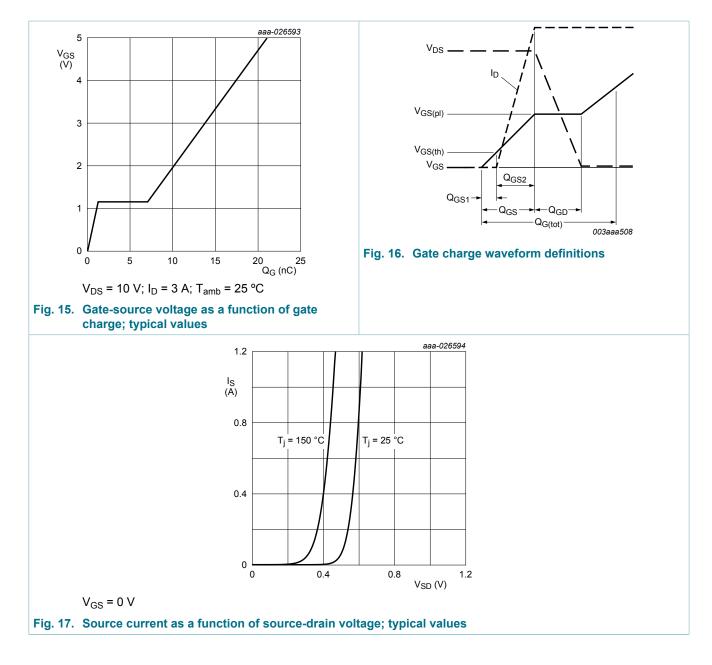
# PMCM6501UNE

#### 20 V, N-channel Trench MOSFET

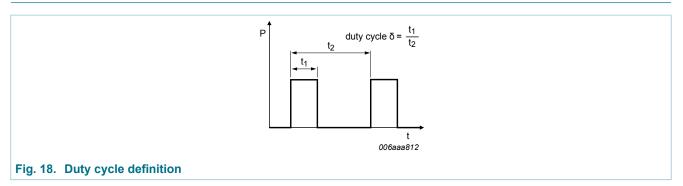


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#### 20 V, N-channel Trench MOSFET

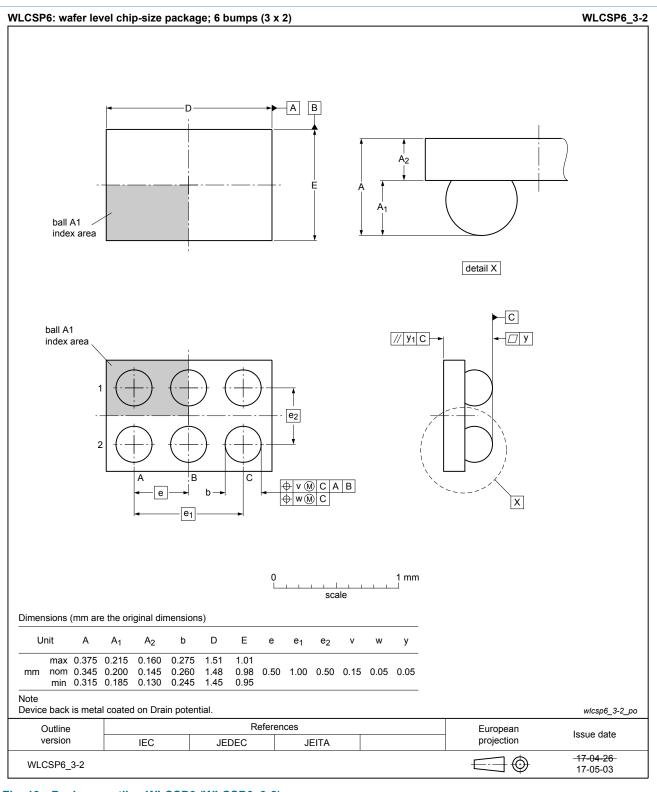


# **11. Test information**



#### 20 V, N-channel Trench MOSFET

#### 12. Package outline

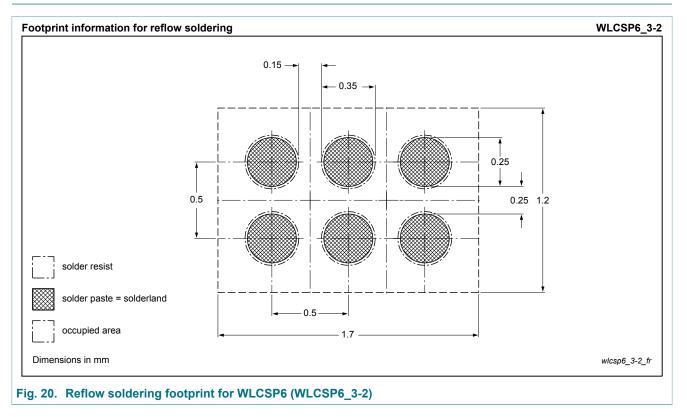


#### Fig. 19. Package outline WLCSP6 (WLCSP6\_3-2)

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# 13. Soldering



#### 20 V, N-channel Trench MOSFET

# 14. Revision history

| Table 8. Revision history |              |                    |               |            |  |  |
|---------------------------|--------------|--------------------|---------------|------------|--|--|
| Data sheet ID             | Release date | Data sheet status  | Change notice | Supersedes |  |  |
| PMCM6501UNE v.1           | 20170530     | Product data sheet | -             | -          |  |  |

#### 20 V, N-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

| Document<br>status [1][2]            | Product<br>status [3] | Definition  |
|--------------------------------------|-----------------------|---|
| Objective<br>[short] data<br>sheet   | Development           | This document contains data from<br>the objective specification for product<br>development. |
| Preliminary<br>[short] data<br>sheet | Qualification         | This document contains data from the preliminary specification.                             |
| Product<br>[short] data<br>sheet     | Production            | This document contains the product specification.   |

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